



Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Isolated plastic package
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	e maximum rating						
V_{RRM}	repetitive peak reverse voltage			600			V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _h = 47 °C; Fig. 1; Fig. 2		8		A	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _h ≤ 47 °C; square-wave pulse		16		A	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	55 60			A	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				А	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>		-	2	2.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	1.5	1.85	V
Dynamic	characteristics			,			
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$		-	20	-	ns

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		КҢА
mb	n.c.	mounting base; isolated	SOD113 (2-lead TO-220F)	001aaa020

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BYC8DX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113			

7. Marking

Table 4. Marking codes	
Type number	Marking codes
BYC8DX-600	BYC8DX-600

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V _{RWM}	crest working reverse voltage		600	V
V _R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; T _h = 47 °C; Fig. 1; Fig. 2	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _h ≤ 47 °C; square-wave pulse	16	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	55	А
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	60	А
T _{stg}	storage temperature		-40 to 150	°C
Tj	junction temperature		150	°C

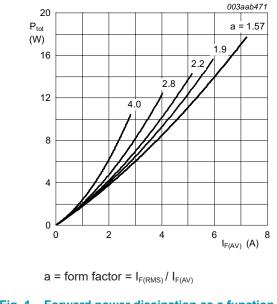
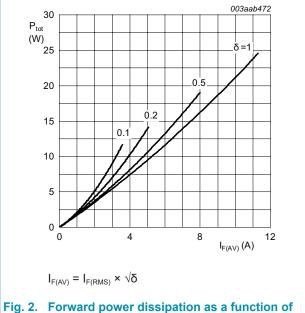


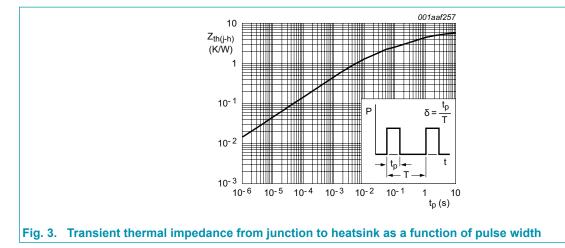
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



 ig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)} thermal resistance from junction to heatsink		without heatsink compound	-	-	7.2	K/W
		with heatsink compound; Fig 3	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

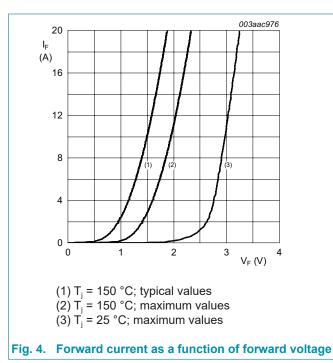


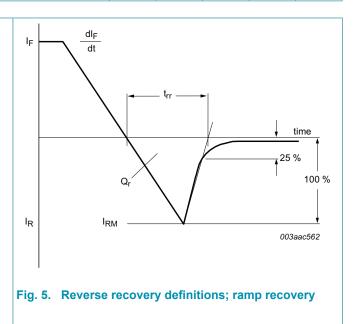
10. Isolation characteristics

Fable 7. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink		-	10	-	pF

11. Characteristics

Table 8. Cl	naracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>	-	2	2.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.5	1.85	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	9	40	μA
		V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 1 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$	-	13	-	nC
t _{rr} re	reverse recovery time	$I_{F} = 8 \text{ A}; V_{R} = 400 \text{ V}; \text{d}_{\text{F}}/\text{d}\text{t} = 500 \text{ A}/\mu\text{s}; \\ T_{j} = 100 ^{\circ}\text{C}; \underline{\text{Fig. 5}}$	-	32	40	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 5}$	-	30	52	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 5}$		20	-	ns
I _{RM}	peak reverse recovery current	$\begin{array}{l} I_{F} = 10 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/\text{d}t = 500 \text{ A}/\mu\text{s}; \\ T_{j} = 100 ^{\circ}\text{C} \end{array}$	-	9.5	12	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}$	-	1.5	5.5	А
V_{FR}	forward recovery voltage	I _F = 10 A; dI _F /dt = 100 A/μs; T _j = 25 °C; <u>Fig. 6</u>	-	8	10	V

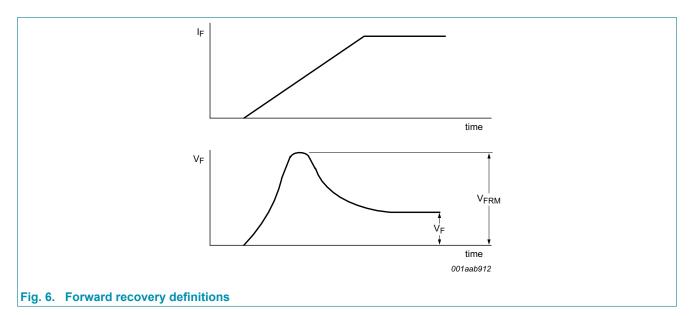




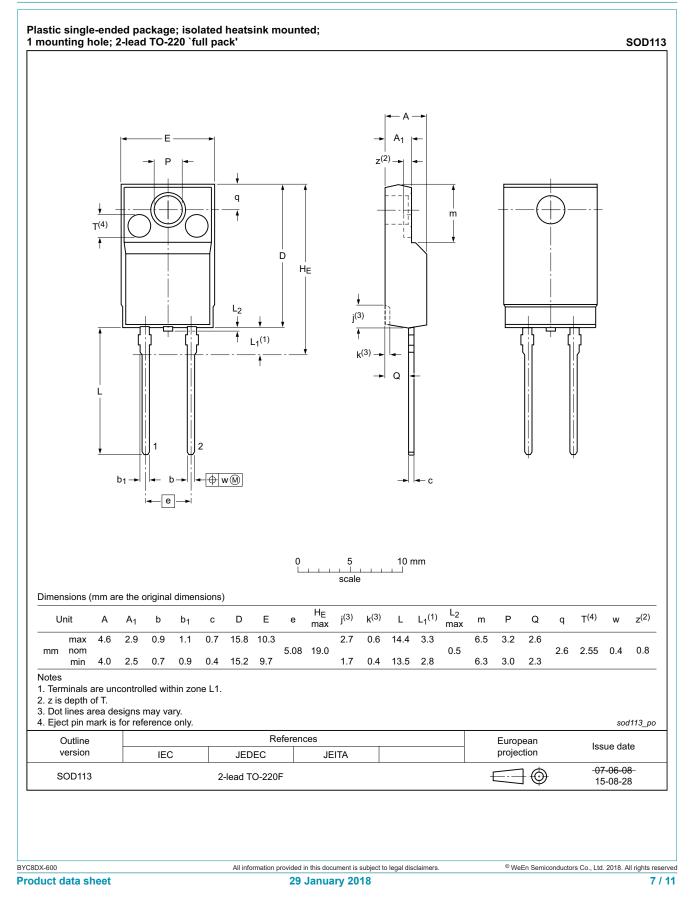
WeEn Semiconductors

BYC8DX-600

Hyperfast power diode



12. Package outline



13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BYC8DX-600 v.2	20180129	Product data sheet	-	BYC8DX-600 v.1	
Modifications: Change from NXP version to WeEn version					
BYC8DX-600 v.1	20101227	Product data sheet	-	-	

BYC8DX-600

Hyperfast power diode

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BYC8DX-600 Hyperfast power diode

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	Features and benefits

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